

Title of Change:	Update datasheet for adding the dependent on switching time characteristics and input pulse width.
Effective date:	15 December 2016
Contact information:	Contact your local ON Semiconductor Sales Office or <Osamu Akaki@onsemi.com>
Type of notification:	ON Semiconductor will consider this change accepted.
Change category:	<input type="checkbox"/> Wafer Fab Change <input type="checkbox"/> Assembly Change <input type="checkbox"/> Test Change <input checked="" type="checkbox"/> Other Datasheet Update

Change Sub-Category(s):	<input checked="" type="checkbox"/> Datasheet/Product Doc change
<input type="checkbox"/> Manufacturing Site Change/Addition	<input type="checkbox"/> Shipping/Packaging/Marking
<input type="checkbox"/> Manufacturing Process Change	<input type="checkbox"/> Other: _____
<input type="checkbox"/> Material Change	
<input type="checkbox"/> Product specific change	

Sites Affected:	<input checked="" type="checkbox"/> All site(s) <input type="checkbox"/> not applicable <input type="checkbox"/> ON Semiconductor site(s) : <input type="checkbox"/> External Foundry/Subcon site(s)
------------------------	--

Description and Purpose:

This Product Bulletin updates the datasheet in order to add characteristics suitable for the customer's application use. Updating this datasheet does not change other characteristics of the current datasheet.

Add the following 4 points

- 1) Switching time PW>10ms value. (Page.2)
- 2) Switching time circuit of PW>10ms. (Page.2)
- 3) Note 3 : The fall switching time is dependent on the input pulse width. (Page.2)
- 4) Dependency graph of switching time and input pulse width. (Page.3)

The below examples are ECH8693R-TL-W.

Turn-ON Delay Time	$t_{d(on)}$	See Fig. 1 (Note 3)	545	ns
Rise Time	t_r		525	ns
Turn-OFF Delay Time	$t_{d(off)}$		18,65	μ s
Fall Time	t_f	See Fig. 2 (Note 3)	22,2	μ s
Turn-ON Delay Time	$t_{d(on)}$		545	ns
Rise Time	t_r		525	ns
Turn-OFF Delay Time	$t_{d(off)}$		1,130	μ s
Fall Time	t_f		410	μ s
Total Gate Charge	Q_g		13	nC
Gate to Source Charge	Q_{gs}	$V_{DS} = 10\text{ V}, V_{GS} = 4.5\text{ V}, I_D = 14\text{ A}$	3	nC
Gate to Drain "Miller" Charge	Q_{gd}		2.4	nC
Forward Diode Voltage	V_{SD}		$I_S = 14\text{ A}, V_{GS} = 0\text{ V}$	0.78

Note 2 : Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.
 Note 3 : The fall switching time is dependent on the input pulse width.

Fig.1 Switching Time Test Circuit 1

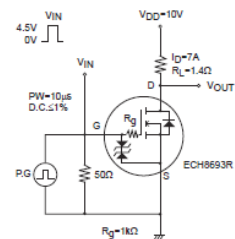
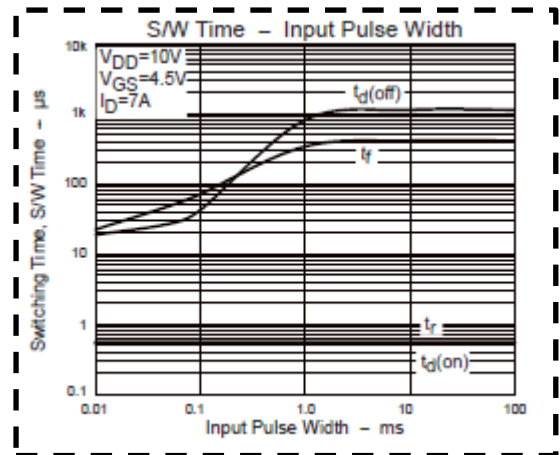
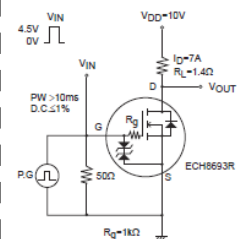


Fig.2 Switching Time Test Circuit 2



List of affected Standard Parts:

- ECH8693R-TL-W
- ECH8695R-TL-W
- ECH8697R-TL-W